

PNP Epitaxial Silicon Transistor

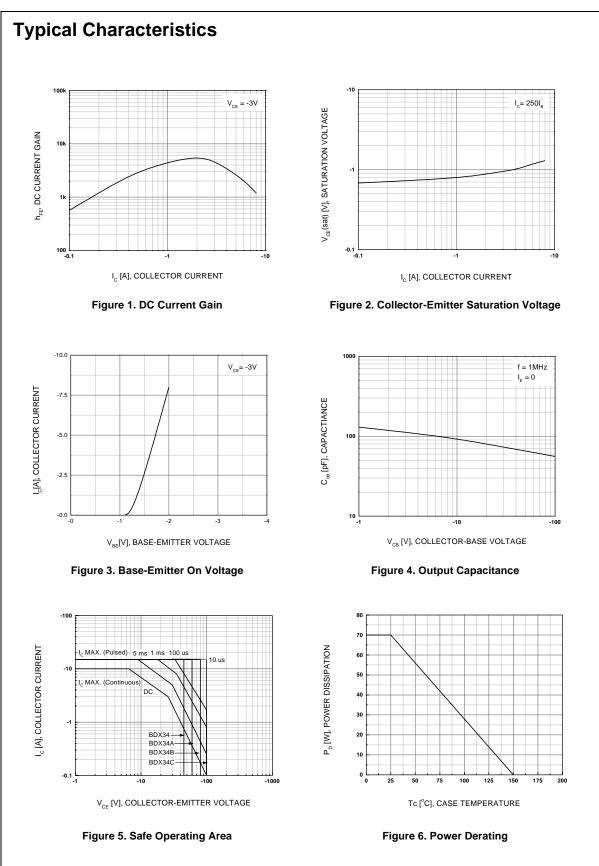
Absolute Maximum Ratings T_C=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | | |
| 020 | : BDX34 | - 45 | V |
| | : BDX34A | - 60 | V |
| | : BDX34B | - 80 | V |
| | : BDX34C | - 100 | V |
| V _{CEO} | Collector-Emitter Voltage | | 54 |
| | : BDX34 | - 45 | V |
| | : BDX34A | - 60 | Vent |
| | : BDX34B | - 80 | V |
| | : BDX34C | - 100 | V |
| Ι _C | Collector Current (DC) | - 10 | A |
| I _{CP} | *Collector Current (Pulse) | - 15 | A |
| Ι _Β | Base Current | - 0.25 | A |
| P _C | Collector Dissipation (T _C =25°C) | 70 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C |

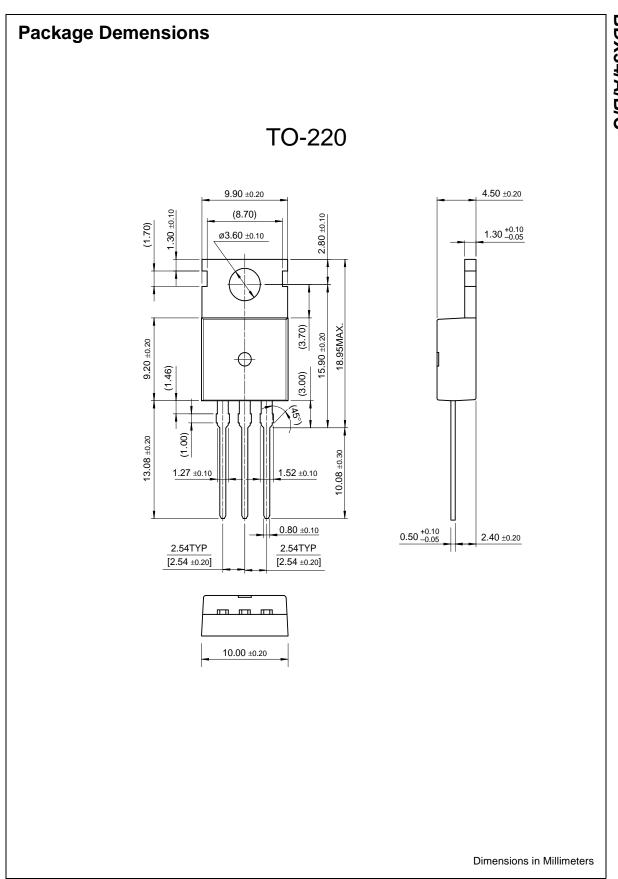
| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|------------------------|--|--|-------|------|----------------|----------|
| V _{CEO} (sus) | * Collector-Emitter Sustaining Voltage | | | | | |
| | : BDX34 | I _C = -100mA, I _B = 0 | - 45 | | | V |
| | : BDX34A | - | - 60 | | | V |
| | : BDX34B | | - 80 | | | V |
| | : BDX34C | | - 100 | | | V |
| V _{CER} (sus) | * Collector-Emitter Sustaining Voltage | | | | | |
| | : BDX34 | I _C = -1 00mA, I _B = 0 | - 45 | | | V |
| | : BDX34A | R _{BE} = 100Ω | - 60 | | | V |
| | : BDX34B | | - 80 | | | V |
| | : BDX34C | | - 100 | | | V |
| V _{CEV} (sus) | * Collector-Emitter Sustaining Voltage | | | | | |
| | : BDX34 | I _C = - 100mA, I _B = 0 | - 45 | | | V |
| | : BDX34A | V _{BE} = - 1.5V | - 60 | | | V |
| | : BDX34B | | - 80 | | | V |
| | : BDX34C | | - 100 | | | V |
| I _{CBO} | Collector Cut-off Current | | | | | |
| | : BDX34 | $V_{CB} = -45V, I_E = 0$ | | | - 0.2 | mA |
| | : BDX34A | $V_{CB} = -60V, I_E = 0$ | | | - 0.2 | mA |
| | : BDX34B | $V_{CB} = -80V, I_E = 0$ | | | - 0.2 | mA |
| | : BDX34C | V _{CB} = - 100V, I _E = 0 | | | - 0.2 | mA |
| I _{CEO} | Collector Cut-off Current : BDX34 | | | | 0.5 | |
| | : BDX34 | $V_{CE} = -22V, I_B = 0$ $V_{CE} = -30V, I_B = 0$ | | | - 0.5 - 0.5 | mA mA |
| | : BDX34A | $V_{CE} = -30V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ | | | - 0.5 | mA |
| | : BDX34D | $V_{CE} = -50V, I_B = 0$ | | | - 0.5 | mA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = -5V, I_{C} = 0$ | | | - 5 | mA |
| h _{FE} | * DC Current Gain | | | | - | |
| | : BDX34/34A | V _{CE} = - 3V, I _C = - 4A | 750 | | | |
| | : BDX34B/34C | $V_{CE} = -3V, I_{C} = -3A$ | 750 | | | |
| V _{CE} (sat) | * Collector-Emitter Saturation Voltage | • | | | | |
| | : BDX34/34A | I _C = - 4A, I _B = - 8mA | | | - 2.5 | V |
| | : BDX34B/34C | I _C = - 3A, I _B = - 6mA | | | - 2.5 | V |
| V _{BE} (on) | * Base-Emitter ON Voltage | | | | | |
| | : BDX34/34A | $V_{CE} = -3V, I_{C} = -4A$ | | | - 2.5 | V |
| | : BDX34B/34C | $V_{CE} = -3V, I_{C} = -3A$ | | | - 2.5 | V |
| V _F | * Parallel Diode Forward Voltage | I _F = - 8A | | | - 4 | V |

BDX34/A/B/C

* Pulse Test: PW=300μs, duty Cycle =1.5% Pulsed



BDX34/A/B/C



BDX34/A/B/C

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